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BLX98

U.H.F. LINEAR POWER TRANSISTOR

N-P-N silicon planar epitaxial transistor primarily intended for use in linear u.h.f. amplifiers of television transposers and transmitters in band IV-V.

Features:
- diffused emitter ballasting resistors for an optimum temperature profile;
- gold metallization ensures excellent reliability.

The transistor has a ¼" capstan envelope with a moulded cap. All leads are isolated from the stud.

QUICK REFERENCE DATA

R.F. performance in linear amplifier

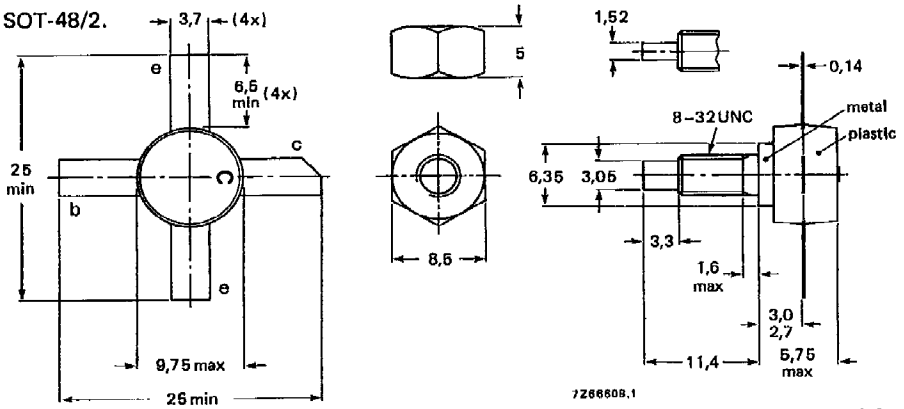
mode of operation	f_{vision} MHz	V_{CE} V	I_C mA	T_h °C	d_{im}* dB	$P_{o\,sync}$* W	G_p dB
class-A	860	25	850	70	−60	> 3,5	> 5,0
class-A	860	25	850	70	−60	typ. 4,0	typ. 5,5

* Three-tone test method (vision carrier −8 dB, sound carrier −7 dB, sideband signal −16 dB), zero dB corresponds to peak sync level.

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-48/2.



Torque on nut: min. 0,75 Nm (7,5 kg cm)
max. 0,85 Nm (8,5 kg cm)

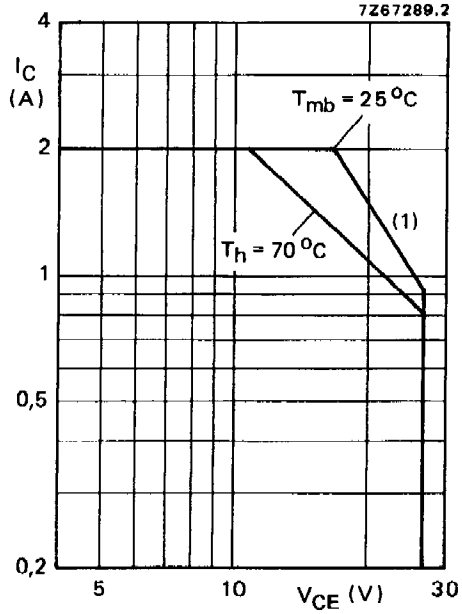
Diameter of clearance hole in heatsink: max. 4,2 mm.
Mounting hole to have no burrs at either end.
De-burring must leave surface flat; do not chamfer or countersink either end of hole.

When locking is required an adhesive is preferred instead of a lock washer.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (peak value); $V_{BE} = 0$	V_{CESM}	max.	50 V
open base	V_{CEO}	max.	27 V
Emitter-base voltage (open collector)	V_{EBO}	max.	3,5 V
Collector current d.c.	I_C	max.	2 A
(peak value); $f > 1$ MHz	I_{CM}	max.	4 A
Total power dissipation at $T_h = 70\ ^oC$	P_{tot}	max.	21,5 W
Storage temperature	T_{stg}		−65 to + 200 °C
Junction temperature	T_j	max.	200 °C



(1) Second breakdown limit (independent of temperature.

Fig. 2 D.C. SOAR.

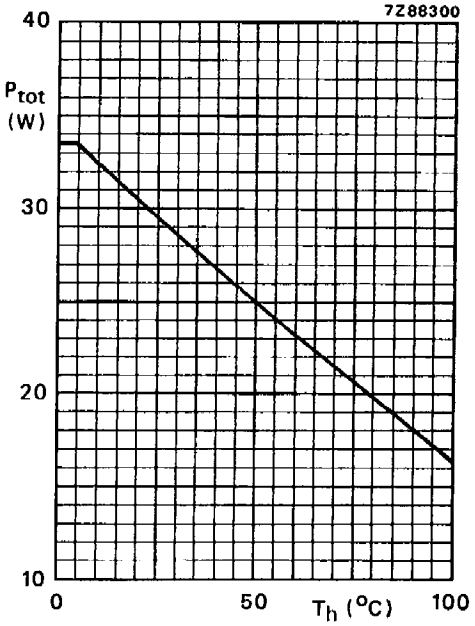


Fig. 3 Power derating curve vs. temperature.

THERMAL RESISTANCE (dissipation = 21,25 W; T_{mb} = 82,75 °C, i.e. T_h = 70 °C).

From junction to mounting base	$R_{th\ j\text{-}mb}$	=	5,45 K/W
From mounting base to heatsink	$R_{th\ mb\text{-}h}$	=	0,6 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector-emitter breakdown voltage			
V_{BE} = 0; I_C = 10 mA	$V_{(BR)CES}$	>	50 V
open base; I_C = 25 mA	$V_{(BR)CEO}$	>	27 V
Emitter-base breakdown voltage			
open collector; I_E = 5 mA	$V_{(BR)EBO}$	>	3,5 V
D.C. current gain*			
I_C = 850 mA; V_{CE} = 25 V	h_{FE}	>	15
		typ.	40
Collector-emitter saturation voltage*			
I_C = 500 mA; I_B = 100 mA	V_{CEsat}	typ.	0,25 V
Transition frequency at f = 500 MHz**			
$-I_E$ = 850 mA; V_{CB} = 25 V	f_T	typ.	2,5 GHz
Collector capacitance at f = 1 MHz			
$I_E = I_e$ = 0; V_{CB} = 25 V	C_c	typ.	24 pF
		<	30 pF
Feedback capacitance at f = 1 MHz			
I_C = 50 mA; V_{CE} = 25 V	C_{re}	typ.	15 pF
Collector-stud capacitance	C_{cs}	typ.	2 pF

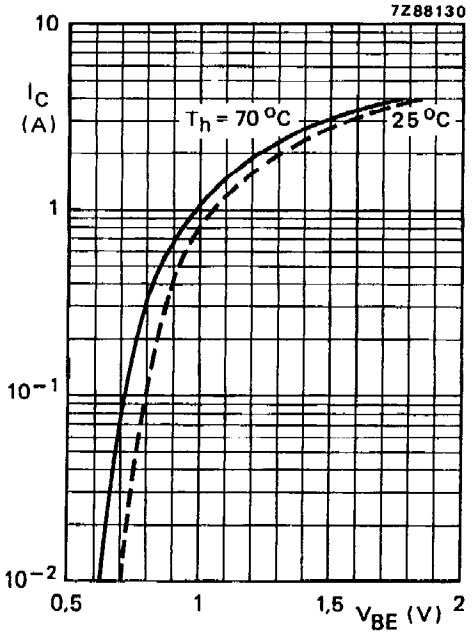


Fig. 5 Typical values; V_{CE} = 25 V.

* Measured under pulse conditions: $t_p \leq 300\ \mu s$; $\delta \leq 0{,}02$.
** Measured under pulse conditions: $t_p \leq 50\ \mu s$; $\delta \leq 0{,}01$.

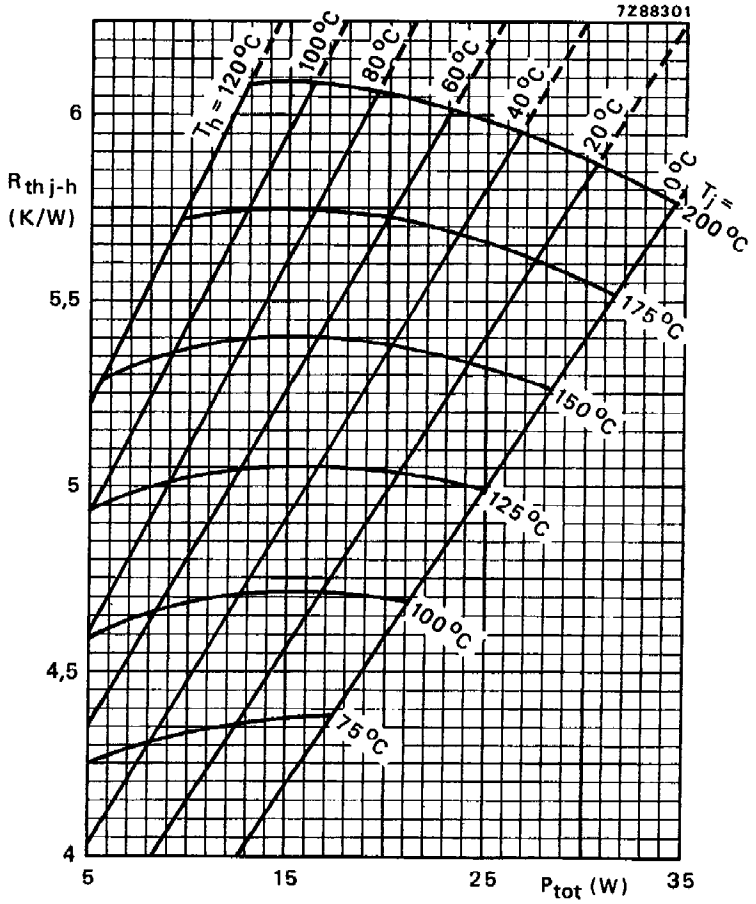


Fig. 4 Maximum thermal resistance from junction to heatsink as a function of power dissipation, with heatsink and junction temperature as parameters. ($R_{th\ mb\text{-}h}$ = 0,6 K/W.)

Example

Nominal class-A operation (without r.f. signal): V_{CE} = 25 V; I_C = 850 mA; T_h = 70 °C.

Fig. 4 shows: $R_{th\ j\text{-}h}$ max. 6,05 K/W
T_j max. 200 °C

Typical device: $R_{th\ j\text{-}h}$ typ. 5,35 K/W
T_j typ. 183 °C